



Schottky Barrier Diode

Features

1. High reliability
2. Very low forward voltage
3. Small surface mounting type



Applications

Applications where a very low forward voltage is required

Absolute Maximum Ratings

T_j=25°C

| Parameter | Test Conditions | Symbol | Value | Unit |
|-------------------------------------|----------------------------------------------|------------------|----------|------|
| Repetitive peak reverse voltage | | V _{RRM} | 40 | V |
| Forward continuous current | T _{amb} =25°C | I _F | 350 | mA |
| Repetitive peak forward current | T _{amb} =25°C, t _p ≤1 s | I _{FRM} | 1 | A |
| Surge forward current | t _p ≤10ms, T _{amb} =25°C | I _{FSM} | 7.5 | A |
| Power dissipation | T _{amb} =65°C | P _{tot} | 330 | mW |
| Maximum junction temperature | | T _j | 125 | °C |
| Ambient operating temperature range | | T _A | -65~+125 | °C |
| Storage temperature range | | T _{stg} | -65~+150 | °C |

Stresses exceeding maximum ratings may damage the device. Maximum ratings are stress ratings only. Functional operation above the recommended operating conditions is not implied. Extended exposure to stresses above the recommended operating conditions may affect device reliability.

Excel Semiconductor



Electrical Characteristics

$T_j=25^\circ\text{C}$

| Parameter | Symbol | Test Conditions | Min | Typ | Max | Unit |
|-----------------------------------------------------------------------|--------------------|----------------------------------------|-----|-----|------|---------------|
| Reverse breakdown voltage | $V_{(\text{BR})R}$ | $I_R=10\mu\text{A}$ (pulsed) | 40 | - | - | V |
| Leakage Current Pulse test $t_p < 300\mu\text{s}$, $\delta < 2\%$ | I_R | $V_R=10\text{V}$ | - | - | 2 | μA |
| | | $V_R=10\text{V}, T_j=60^\circ\text{C}$ | - | - | 15 | μA |
| | | $V_R=20\text{V}$ | - | - | 5 | μA |
| | | $V_R=20\text{V}, T_j=60^\circ\text{C}$ | - | - | 25 | μA |
| | | $V_R=40\text{V}$ | - | - | 25 | μA |
| | | $V_R=40\text{V}, T_j=60^\circ\text{C}$ | - | - | 50 | μA |
| Forward voltage Pulse test $t_p < 300\mu\text{s}$, $\delta < 2\%$ | V_F | $I_F=0.1\text{mA}$ | - | - | 0.25 | V |
| | | $I_F=1\text{mA}$ | - | - | 0.30 | V |
| | | $I_F=10\text{mA}$ | - | - | 0.40 | V |
| | | $I_F=50\text{mA}$ | - | - | 0.50 | V |
| | | $I_F=200\text{mA}$ | - | - | 0.75 | V |
| | | $I_F=500\text{mA}$ | - | - | 0.90 | V |
| Capacitance | C_{tot} | $V_R=1\text{V}, f=1\text{MHz}$ | - | 12 | - | pF |

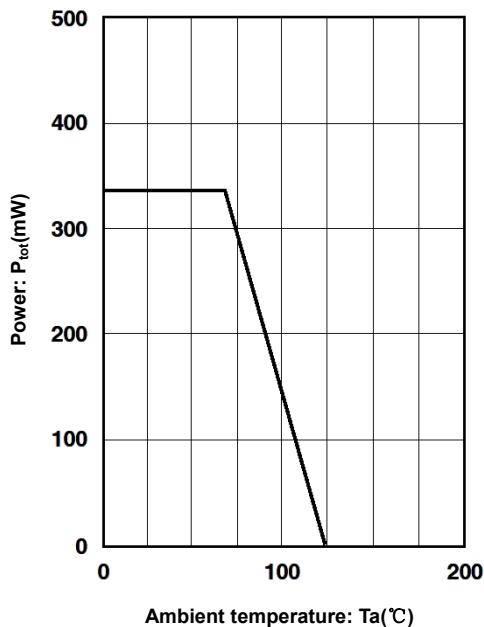
**Characteristics ($T_j=25^\circ\text{C}$ unless otherwise specified)**

Figure 1. Admissible power dissipation
vs. ambient temperature

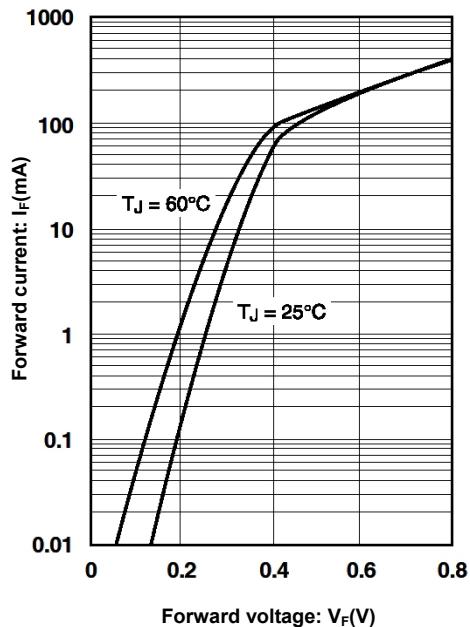


Figure 2. Forward characteristics

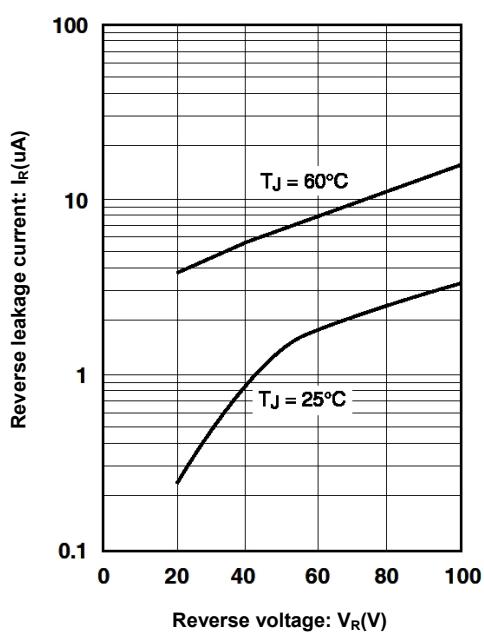
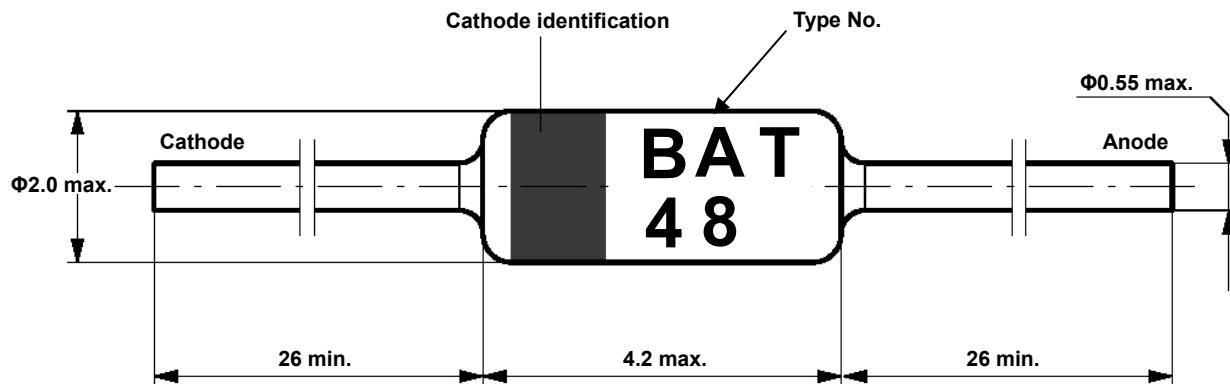


Figure 3. Typical reverse characteristics

Excel Semiconductor

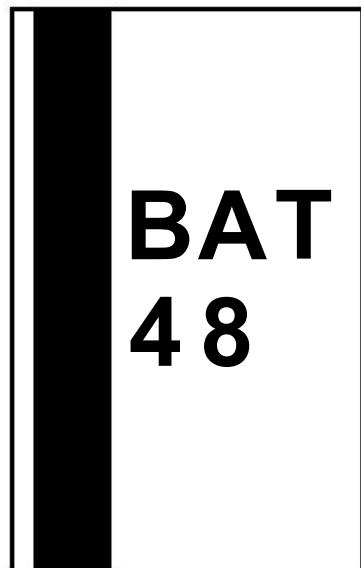


Dimensions in mm



Standard Glass Case
JEDEC DO-35

Marking



Excel Semiconductor